

isc Silicon PNP Power Transistor

2SA614

**DESCRIPTION**

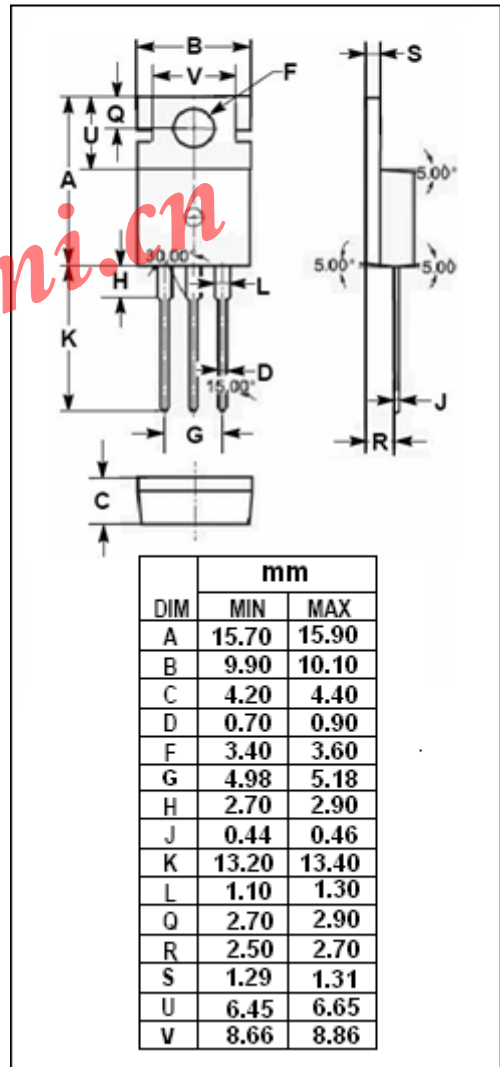
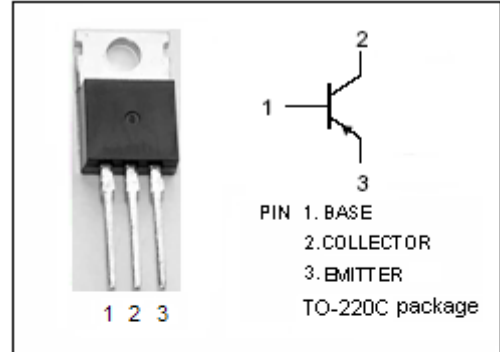
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -55V$  (Min.)
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = -0.5V$  (Max.) @  $I_C = -1A$
- Collector Power Dissipation-  
:  $P_C = 25W$  @  $T_C = 25^\circ C$

**APPLICATIONS**

- Designed for medium power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-55	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-3	A
$P_C$	Collector Power Dissipation	25	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



## isc Silicon PNP Power Transistor

2SA614

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-55			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -500\ \mu\text{A}; I_E = 0$	-80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -500\ \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}; I_B = -0.1\text{A}$			-0.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-50	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5; I_C = 0$			-50	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -5\text{V}$	40		240	

◆  $h_{FE}$  Classifications

R	O	Y
40-80	70-140	120-240